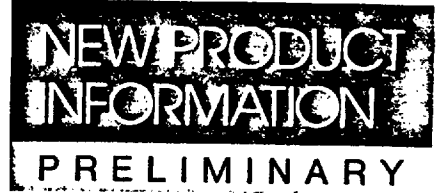


T-42-11-09

SHARP**LZ9A Series**High Density
Channel-free Gate Array (Sea-of-gate)

■ Description

The LZ9A series is a channel-free gate array fabricated using silicon gate CMOS process technology.

It is developed to meet user's requirements such as large scale, high speed, high performance and multi-I/O function, which are suitable to consumer appliances to industrial equipment.

Furthermore, Sharp offers powerful lineup of cell libraries compatible with those of the LZ98 series, along with memory cells and peripheral macro cells.

■ Features

1. CMOS process
2. Sea-of-gate structure
3. Total gate count: 30000, 50000, 60000, 80000, 100000, 150000, 200000
4. Delay time: 0.4ns/gate (F.O. = 2, $\ell = 2\text{mm}$)
5. Output current: 12mA
6. Supply voltage: 2.0 to 5.5V
7. Usable gate count: 60%
8. Memory cell
 - ROM: 64K bits (MAX.)
 - RAM: 16K bits (MAX.)

■ LZ9A Series Lineup

Model No.	LZ9A30000	LZ9A50000	LZ9A60000	LZ9A80000	LZ9A100000	LZ9A150000	LZ9A200000
Total gate count	30000	50000	60000	80000	100000	150000	200000
Usable gate count	1800	30000	36000	48000	60000	90000	120000
I/O buffers	212	246	268	300	334	400	450
Process	0.8 μm CMOS						
Delay time	Internal gate	0.4ns (F.O. = 2 $\ell = 2\text{mm}$)					
	Input buffer	1.4ns					
	Output buffer	1.8ns					
I/O level	CMOS/TTL						
Supply voltage	2.0 to 5.5V						

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LZ9A Series

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■ Electrical Characteristics

Parameter	Symbol	Conditions	TTL level			CMOS level			Unit
			MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Input LOW voltage	V_{IL}				0.8			1.5	V
Input HIGH voltage	V_{IH}		2.0			3.5			V
Input HIGH threshold voltage	V_{T+}	Schmitt input buffer			2.2			3.7	V
Input LOW threshold voltage	V_{T-}	Schmitt input buffer	0.5			1.0			V
Hysteresis voltage	$V_{T+} - V_{T-}$	Schmitt input buffer	0.2			0.4			V
Output LOW voltage	V_{OL}	$I_{OL} = 1, 2, 4, 6, 8, 12\text{mA}$			0.4			0.4	V
Output HIGH voltage	V_{OH}	$I_{OH} = -0.5, -1, -2, -3, -4, -6\text{mA}$	4.0			4.0			V
Input leakage current	I_i	$V_i = 0V - V_{CC}$	-1.0		1.0	-1.0		1.0	μA
Output leakage current	I_{OZ}	Output high impedance	-1.0		1.0	-1.0		1.0	μA
Input LOW current	$ I_{OL} $	$V_i = 0V$	8	20	60	8	20	60	μA
Input HIGH current	I_{OH}	$V_i = V_{CC}$	8	20	60	8	20	60	μA

■ Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Supply voltage	V_{CC}	-0.3 to 6.0	V
Input voltage	V_i	-0.3 to $V_{CC} + 0.3$	V
Output voltage	V_O	-0.3 to $V_{CC} + 0.3$	V
Operating temperature	T_{opr}	-40 to +85	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

■ Recommended Operating Conditions

Parameter	Symbol	TTL level			CMOS level			Unit
		MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Supply voltage	V_{CC}	4.75	5	5.25	4.5	5	5.5	V
Operating temperature	T_{opr}	-40		+85	-40		+85	$^{\circ}\text{C}$

Macro Cell Library

Basic Macro Cells

Name	Function	Gate count
Inverters, non-inverters		
INV1	Single drive inverter	1
INV2	Double drive inverter	1
INV3	Tripple drive inverter	2
INV4	Quad drive inverter	2
INV6	6 times drive inverter	3
INV1P	Single drive inverter Pch Tr. PARA.	1
INV2P	Double drive inverter Pch Tr. PARA.	2
INV4P	Quad drive inverter Pch Tr. PARA.	4
NIN1	Single drive non-inverter	1
NIN2	Double drive non-inverter	2
NIN3	Triple drive non-inverter	2
NIN4	Quad drive non-inverter	3
Internal bus buffers, delay elements		
CINV	Active high clocked inverter (Half drive internal bus buffer)	2
CXINV	Active low clocked inverter (Half drive internal bus buffer)	2
INTB1	Single drive internal bus buffer	3
INTB2	Double drive internal bus buffer	4
INTB4	Quad drive internal bus buffer	5
DLY10	10nsec delay (App.)	12
DLY20	20nsec delay (App.)	24
DLY40	40nsec delay (App.)	48
NAND/NOR gates		
NA2	2-input NAND gate	1
NA3	3-input NAND gate	2
NA4	4-input NAND gate	2
NA5	5-input NAND gate	4
NA6	6-input NAND gate	5
NA7	7-input NAND gate	5
NA8	8-input NAND gate	6
NA2P	2-input POWER NAND gate	2
NA3P	3-input POWER NAND gate	3
NA4P	4-input POWER NAND gate	4
NO2	2-input NOR gate	1
NO3	3-input NOR gate	2
NO4	4-input NOR gate	2
NO5	5-input NOR gate	4
NO6	6-input NOR gate	4
NO7	7-input NOR gate	5
NO8	8-input NOR gate	5
NO2P	2-input POWER NOR gate	6
NO3P	3-input POWER NOR gate	2
NO4P	4-input POWER NOR gate	3
AND/OR/EX-NOR gates		
AN2	2-input AND gate	2
AN3	3-input AND gate	2
AN4	4-input AND gate	3
OR2	2-input OR gate	2
OR3	3-input OR gate	2
OR4	4-input OR gate	3

LZ9A Series High Density Channel-free Gate Array (Sea-of-gate)

CPU Peripheral Macro Cells

Name	Function	Gate count
DMAC	Direct Memory Access Controller	5482 + α
UART	Universal Asynchronous Receiver and Transmitter	3015 + α
USART	Universal Synchronous/Asynchronous Receiver and Transmitter	2500 + α
PIT	Programmable Internal Timer	3516 + α
PIO	Parallel I/O	2056 + α
PIC	Programmable Interrupt Controller	2209 + α
CG	Clock Generator	111 + α
BUSC	Bus Controller	572 + α

α : gates for test circuits

I/O Buffer Cells

Standard I/O Cells (Cells with pull-up/pull-down resistors are also available.)

Name	Function	Gate count
Special input cells		
IBF	TTL level input buffer	1
IBFC	CMOS level input buffer	1
IBFS	TTL level schmitt-trigger input buffer	1
IBFCS	CMOS level schmitt-trigger input buffer	1
Special output cells		
OBF	Output buffer $I_{OL} = 4\text{mA}$ ($I_{OH} = -2\text{mA}$)	0
OBF1M	Output buffer $I_{OL} = 1\text{mA}$ ($I_{OH} = -0.5\text{mA}$)	0
OBF2M	Output buffer $I_{OL} = 2\text{mA}$ ($I_{OH} = -1\text{mA}$)	0
OBF6M	Output buffer $I_{OL} = 6\text{mA}$ ($I_{OH} = -3\text{mA}$)	0
OBF8M	Output buffer $I_{OL} = 8\text{mA}$ ($I_{OH} = -4\text{mA}$)	0
OBF10M	Output buffer $I_{OL} = 10\text{mA}$ ($I_{OH} = -5\text{mA}$)	0
OBF12M	Output buffer $I_{OL} = 12\text{mA}$ ($I_{OH} = -6\text{mA}$)	0
TOBF (4mA)	Output buffer $I_{OL} = 4\text{mA}$ ($I_{OH} = -2\text{mA}$, 3-state output)	0
OBFN (4mA)	Output buffer $I_{OL} = 4\text{mA}$ (Nch open drain output)	0
OBFP (2mA)	Output buffer $I_{OH} = 2\text{mA}$ (Pch open drain output)	0
Common I/O cell		
IOBF (4mA)	TTL level input and $I_{OL} = 4\text{mA}$ ($I_{OH} = 2\text{mA}$) output buffer	1
IOBFC (4mA)	CMOS level input and $I_{OL} = 4\text{mA}$ ($I_{OH} = 2\text{mA}$) output buffer	1
Special I/O cells		
OSC	Oscillator with IBF0 (Drive factor 4)	1
OSC1M	Oscillator with IBF0 (Drive factor 1)	1
OSC2M	Oscillator with IBF0 (Drive factor 2)	1
OSCL	Low power oscillator (with IBF0)	1
ASW	Analog switch (with OBF0)	0
OBF0	Analog switch (with ASW)	0
IBF0	Oscillator with OSC, OSC1M, OSC2M, or OSCL	0
XIBFC5	5 times drive inverting input buffer	0
XOBF1M	3 PAD C-R oscillator with IBFCS and OSC	0
NABF	Amplifier NAND input buffer with OBF0	0
IOBF0C	Amplifier with NABF	1
BINV5	5 times drive inverter ON I/O cell	0

Name	Function	Gate count
AND/OR/EX-NOR gates		
EXO	2-input EXCLUSIVE OR	3
EXN	2-input EXCLUSIVE NOR	3
Combined logic circuits, combined gate circuits		
ON1	2,1 input OR-NAND gate	2
DN1	2,1 input AND-NOR gate	2
DN22	2×2 input AND-NOR gate	2
OA1	2,1 input OR-AND gate	2
OA22	2×2 input OR-AND gate	3
AO1	2,1 input AND-OR gate	2
AO22	2×2 input AND-OR gate	3
AO23	2×3 input AND-OR gate	4
AO24	2×4 input AND-OR gate	5
AO25	2×5 input AND-OR gate	6
AO26	2×6 input AND-OR gate	7
AO32	3×2 input AND-OR gate	4
AO33	3×3 input AND-OR gate	5
AO34	3×4 input AND-OR gate	7
AO42	4×2 input AND-OR gate	5
AO43	4×3 input AND-OR gate	7
AO52	5×2 input AND-OR gate	7
AON	2,1,1 input AND-OR-NAND gate	2
OAN	2,1,1 input OR-AND-NOR gate	2
DS	2 to 1 data selector	3
DSN	2 to 1 inverting data selector	3
ADDH	Half adder	4
ADDF	Full adder	7
Latch, flip-flop cells		
DLT	D latch	4
DLTR	D latch with reset	5
D	D flip-flop	6
DR	D flip-flop with reset	8
DRS	D flip-flop with reset & set	10
DRS4	D flip-flop with reset & set	8
DAL3	D flip-flop with asynchronous load	10
TR	T flip-flop with reset	10
JK	JK flip-flop	9
JKRS	JK flip-flop with reset & set	12
Flip-flop cells for ATPG		
SD	D flip-flop for ATPG	8
SDR	D flip-flop with reset for ATPG	9
SDRS	D flip-flop with reset & set for ATPG	11
SDRS4	D flip-flop with reset & set for ATPG	10
SDAL3	D flip-flop with asynchronous load for ATPG	12
STR	T flip-flop with reset for ATPG	11
SJK	JK flip-flop for ATPG	11
SJKRS	JK flip-flop with reset & set for ATPG	13

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■ Packages

Model No.	DIP			SDIP	SOP			PLCC	QFP													
	24	32	40	64	32	40	44	44	60	64	80 (1)	80 (2)	96	100 (3)	100 (4)	128	144	160	184	208	256	
LZ9A30000	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	●	○	○		
LZ9A50000		●	●	●	●	●	●		○	○	●	○	●	●	○	●	○	●	●	●	○	
LZ9A60000							●		○	○	●	○	●	●	○	●	○	●	●	●	○	
LZ9A80000											○		○			●	○	○	○	○	○	
LZ9A100000											○		○			●	●	○	○	○	○	
LZ9A150000											○		○			○	○	○	○	○	○	
LZ9A200000																○	○	○	○	○	○	

●: Available
○: Under development

NOTE:

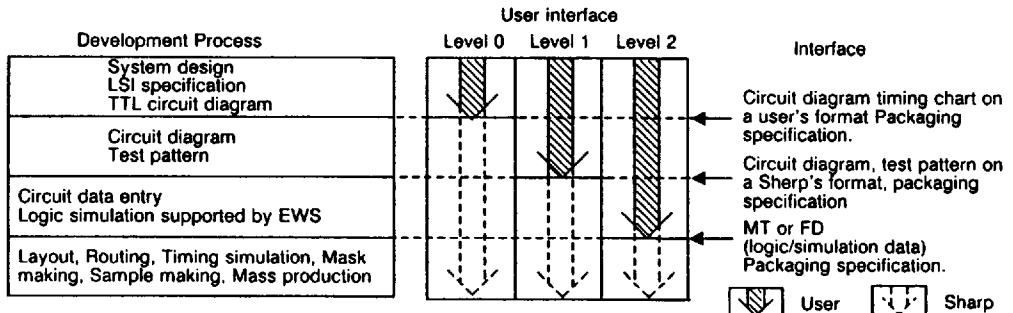
	Nominal dimension	Pin pitch
(1)	18 x 18mm ²	0.8mm
(2)	14 x 20mm ²	0.8mm
(3)	14 x 20mm ²	0.65mm
(4)	14 x 14mm ²	0.5mm

■ Sharp's Product Lineup

Gate scale	LZ98 Series		LZ9A Series	
	Model No.	Gate count	Model No.	Gate count
5000	LZ988000	9000		
	LZ989000	9000		
10000	LZ9811000	11000		
	LZ9812000	12000		
	LZ9813000	13000		
	LZ9816000	16000		
	LZ9817000	17000		
20000	LZ9823000	23000		
	LZ9824000	24000		
30000	LZ9830000	30000	LZ9A30000	30000
50000			LZ9A50000	50000
			LZ9A60000	60000
			LZ9A80000	80000
			LZ9A100000	100000
100000			LZ9A150000	150000
200000			LZ9A200000	200000

■ Support System

● Interface between User and Sharp



■ Support Tools

Support	System	Version
EWS	Mentor IDEA ¹	Ver. 7.0

Support	System	Hardware
Personal computer	Sharp SF-CAD ²	PC8041 (MS-DOS 3.2)
	Workview ³ (Ver. 3.0)	IBM PC-AT (MS-DOS 3.2)

- Notes:
1. IDEA is a trademark of Mentor Graphics.
 2. SF-CAD is sharp's original CAD system.
 3. Workview is a registered trademark of DAISY/CADNETIX.

CPU Peripherals macro Cell			Cell library compatible with LZ98
Peripherals		Gate scale	
82C37	DMAC	5482 + α	· Basic macro cell library
82C50	UART	3015 + α	
82C51	USART	2500 + α	
82C54	PIT	3516 + α	· TTL 74 equivalent cells
82C55	PIO	2056 + α	
82C59	PIC	2209 + α	· ROM
82C84	CG	111 + α	
82C88	BUSC	572 + α	· RAM

α : Additional gates for test circuits with approx. 10% of each gate count, which eliminate tests at user's side.